

**SEMICONDUCTOR
TECHNICAL DATA**

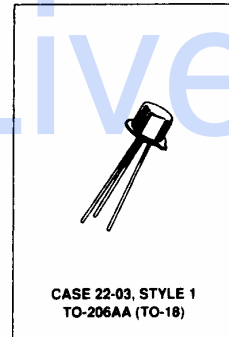
**2N3250A
2N3251A**

**PNP Silicon
Small-Signal Transistors**

designed for general-purpose switching and amplifier applications.

**CRYSTALONCS
2805 Veterans Highway
Suite 14
Ronkonkoma, N.Y. 11779**

MAXIMUM RATINGS			
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	60	Vdc
Collector-Base Voltage	V _{CBO}	60	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current	I _C	200	mAdc
Power Dissipation	P _T		
@ T _A = 25 C		0.36	Watts
Derate above 25 C		2.06	mW/C
@ T _C = 25 C		1.2	Watts
Derate above 25 C		6.9	mW/C
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-65 to 200	C



ELECTRICAL CHARACTERISTICS (T _A = 25 C unless otherwise noted)				
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ⁽¹⁾ (I _C = 10 mAdc)	V _{(BR)CEO}	60	—	Vdc
Collector-Base Breakdown Voltage (I _C = 10 μAdc)	V _{(BR)CBO}	60	—	Vdc
Base-Emitter Voltage (I _E = 10 μAdc)	V _{(BR)EBO}	5.0	—	Vdc
Collector Cutoff Current (V _{CE} = 40 Vdc, V _{EB(off)} = 3.0 Vdc)	I _{CEX}	—	20	nAdc
(V _{CE} = 40 Vdc, V _{EB} = 3.0 Vdc, T _A = 150 C)		—	20	μAdc
Collector Cutoff Current (V _{CB} = 40 Vdc)	I _{CBO}	—	20	nAdc
Emitter Cutoff Current (V _{EB} = 3.0 Vdc, V _{CE} = 40 Vdc)	I _{BEX}	—	50	nAdc

⁽¹⁾ Pulsed Pulse Width 250 to 350 us Duty Cycle 1.0 to 2.0%

Continued

2N3250AJAN, 2N3251AJAN SERIES

ELECTRICAL CHARACTERISTICS — continued (T _A = 25°C unless otherwise noted.)						
Characteristic	Symbol	Min	Max	Unit		
ON CHARACTERISTICS						
DC Current Gain (I _C = 0.1 mA, V _{CE} = 1.0 Vdc)	2N3250A 2N3251A	40	—	—		
		80	—	—		
	(I _C = 1.0 mA)	2N3250A 2N3251A	45	—	—	
			90	—	—	
	(I _C = 10 mA, V _{CE} = 1.0 Vdc) ⁽¹⁾	2N3250A 2N3251A	50	150	—	
100			300	—		
(I _C = 50 mA, V _{CE} = 1.0 Vdc) ⁽¹⁾	2N3250A 2N3251A	15	—	—		
		30	—	—		
(I _C = 1.0 mA, V _{CE} = 1.0 Vdc, T _A = -55°C)	2N3250A 2N3251A	20	—	—		
		40	—	—		
Collector-Emitter Saturation Voltage (I _C = 10 mA, I _B = 1.0 mA) (I _C = 50 mA, I _B = 5.0 mA) ⁽¹⁾	V _{CE(sat)}	—	0.25 0.5	Vdc		
Base-Emitter Saturation Voltage (I _C = 10 mA, I _B = 1.0 mA) (I _C = 50 mA, I _B = 5.0 mA) ⁽¹⁾	V _{BE(sat)}	0.6 —	0.9 1.2	Vdc		
SMALL-SIGNAL CHARACTERISTICS						
Current Gain (I _C = 1.0 mA, V _{CE} = 10 Vdc, f = 1.0 kHz)	2N3250A 2N3251A	h _{re}	50 100	200 400	—	
		Small-Signal Current Transfer Ratio, Magnitude (I _C = 10 mA, V _{CE} = 20 Vdc, f = 100 MHz)	2N3250A 2N3251A	h _{fe}	2.5 3.0	9.0 9.0
Output Capacitance (V _{CB} = 10 Vdc, f = 0.1 to 1.0 MHz)		C _{obo}	—	6.0	pF	
Input Capacitance (V _{EB} = 1.0 Vdc, f = 0.1 to 1.0 MHz) (Output open circuited)		C _{ibo}	—	8.0	pF	
Collector-Base Time Constant (I _C = 10 mA, V _{CE} = 20 Vdc, f = 31.8 MHz)		t _b C _c	5.0	250	ps	
Noise Figure (I _C = 100 μA, V _{CE} = 5.0 Vdc, f = 100 Hz, R _G = 1.0 kohms)		NF	—	6.0	dB	
Voltage Feedback Ratio (I _C = 1.0 mA, V _{CE} = 10 Vdc, f = 1.0 kHz)	2N3250A 2N3251A	h _{re}	—	10 20	X 10 ⁻⁴	
		Input Impedance (I _C = 1.0 mA, V _{CE} = 10 Vdc, f = 1.0 kHz)	2N3250A 2N3251A	h _{ie}	1.0 2.0	6.0 12
Output Admittance (I _C = 1.0 mA, V _{CE} = 10 Vdc, f = 1.0 kHz)	2N3250A 2N3251A	h _{oe}	4.0 10	40 60	μmhos	
		SWITCHING CHARACTERISTICS (See Figure 30) (V _{CC} = 3.0 Vdc, I _C = 10 mA, I _B = 1.0 mA, V _{BE} = 0.5 Vdc)				
Delay Time (V _{BE} = 0.5 Vdc)		t _d	—	35	ns	
Rise Time (V _{BE} = 0.5 Vdc)		t _r	—	35	ns	
Storage Time	2N3250A 2N3251A	t _s	—	175 200	ns	
		Fall Time		t _f	—	50

⁽¹⁾ Pulsed. Pulse Width 250 to 350 μs. Duty Cycle 1.0 to 2.0%.

ASSURANCE TESTING (Pre/Post Burn-In)				
Burn-In Conditions: T_A = 25 ± 3°C, V_{CB} = 25 Vdc, 10 Vdc for JANS				
P_T = 360 mW				
Characteristics Tested	Symbol	Initial and End Point Limits		Unit
		Min	Max	
Collector Cutoff Current (V _{CB} = 40 Vdc)	I _{CBO}	—	20	nA
DC Current Gain ⁽¹⁾ (I _C = 10 mA, V _{CE} = 1.0 Vdc)	2N3250A 2N3251A	h _{FE}	50 100	150 300

Delta from Pre-Burn-In Measured Values		Min	Max	Unit
Delta Collector Cutoff Current	ΔI _{CBO}	—	±100 or ±5.0 whichever is greater	% of Initial Value nA
Delta DC Current Gain ⁽¹⁾	Δh _{FE}	—	±15	% of Initial Value

⁽¹⁾ Pulsed. Pulse Width 250 to 350 μs. Duty Cycle 1.0 to 2.0%.